

FORM PTO-1449
(Rev. 2-32)

U.S. Department of Commerce
Patent and Trademark Office

Atty. Docket No.

05-720-US1

Serial No.

10/559,979

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use several sheets if necessary)

Applicant:

Kouvetakis, et al.

Filing Date:

December 8, 2005

Group:

2814

U.S. PATENT DOCUMENTS

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /SR/

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
/SR/	1.	US 2003-0157787 A1	August 21, 2003	Murthy, et al.			
	2.	US 2006-0134895 A1	June 22, 2006	Kouvetakis, et al.			
	3.	US 2006-0236923 A1	October 26, 2006	Kouvetakis, et al.			
	3.	6,911,084	June 28, 2005	Kouvetakis, et al.			
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/SR/	11.	6,441,716	August 27, 2002	Doppalapudi, et al.			

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Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No

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COMMONLY OWNED CO-PENDING APPLICATIONS

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/SR/	1.	Kouvetakis, et al., U.S. Patent Application No. 10/559,980, Filed on December 8, 2005.
/SR/	2.	Kouvetakis, et al., U.S. Patent Application No. 10/559,981, Filed on September 5, 2006 (Projected Publication date is January 11, 2007).

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